ISSN 0169-4332

applied surface science

A journal devoted to the properties of interfaces
in relation to the synthesis and behaviour of materials

Editors:
L.C. Feldman, Murray Hill, NJ, USA
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MASTER INDEX
Volumes 41–50

ASUSES MI 1-100 (1989)

North-Holland

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Applied Surface Science is published monthly. For 1991, 8 volumes have been announced. The subscription price for these volumes is Dfl. 2360.00 (US$ 1276). Postage and handling amount to Dfl. 240.00 (US$ 130). Therefore the total price is Dfl. 2600.00 (US$ 1406). The price for a combined subscription to the 1991 volumes of Applied Surface Science, Surface Science and Surface Science Reports is Dfl. 9555.00 (US$ 5165), including postage and handling. The Dutch guilder prices are definitive; the currency equivalents are for your guidance only.
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Published Monthly

Printed in The Netherlands

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W.F. van der Weg, Utrecht, The Netherlands

Master Index to Volumes 41–50

NORTH-HOLLAND

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Vanadium oxide

Water
Wetting
Work function

X-ray absorption
X-ray diffraction
X-ray emission
X-ray scattering

Yttrium

Zinc
Zinc oxide
Zirconium

Introduction to Zeolite Science and Practice

edited by **H. van Bekkum,** *TU Delft, Delft, The Netherlands,* **E.M. Flanigen,** *UOP, Tarrytown, NY, USA and* **J.C. Jansen,** *TU Delft, Delft, The Netherlands*

(Studies in Surface Science and Catalysis, 58)

Zeolites and related molecular sieves have quickly become important pathways to new opportunities in the fields of oil processing and petrochemical synthesis. The signs of intense activity in both industry and academia are evident: burgeoning papers and patent applications; increasing numbers of industrial zeolite-based processes and their rapid expansion into organic chemicals manufacturing; recent progress in zeolite accessibility range, matrix behaviour, lattice components and satellite structures; and the recognition that zeolites, which are stable and can be regenerated, may be incorporated into new, environmentally friendly processes.

This volume offers a thorough, up-to-date introduction to zeolites and such related materials as crystalline aluminium phosphates and clays. Its 16 chapters, each written by specialists, provide detailed treatments of zeolite theory (including a review of major developments), zeolite laboratory and research practice, and zeolite industrial applications. Students and individuals entering the field will find **Introduction to Zeolite Science and Practice** a thorough guidebook. Experienced researchers will appreciate its in-depth coverage of the zeolite spectrum, including the latest views on zeolite structure, characterization and applications.

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1991 xvi + 754 pages
Price: Dfl. 395.00 / US$ 225.50
ISBN 0-444-88969-8

Elsevier Science Publishers

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Enrico Fermi International School of Physics, Volume 107

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edited by **G. Scoles**

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Subscr. Price: US $189.50/Dfl.331.50 ISBN 0-444-88331-2

This volume is concerned with the chemical physics of atomic and molecular clusters of medium and large size which are defined as clusters too large to yield rotationally resolved spectra. In practice this means from trimers and tetramers up. By limiting the field a separation is made between the study of systems of well-known structures (for which the position of each of their fragments is well known) from systems that, because of their dynamical or "fluid" status or because of the too large number of components, have to be studied with methods which are intrinsically more statistic.

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The Netherlands

In the USA & Canada:
Elsevier Science Publishing Co., Inc.
P.O. Box 882, Madison Square Station
New York, NY 10159, USA

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[2] S.J. Hoekje and G.B. Hoflund, Appl. Surf. Sci. 47 (1991) 43.
[3] F.J. Himpsel, Surf. Sci. Rep. 12 (1990) 1.
[4] A. Roth, Vacuum Technology, 3rd ed. (North-Holland, Amsterdam, 1990).
[5] V. Celli, in: Dynamical Properties of Solids, Vol. 6, Eds. G.K. Horton and A.A. Maradudin (North-Holland, Amsterdam, 1990) p. 337.

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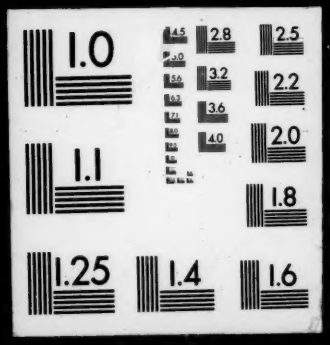
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